

General Purpose Transistor (−50V, −0.15A)

●Dimensions (Unit : mm)

HB50P15CT

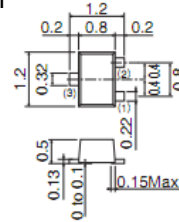
●Features

1) Excellent h_{FE} linearity.

●Structure

Epitaxial planar type.
PNP silicon transistor

HB50P15CT



- (1) Base
- (2) Emitter
- (3) Collector

Abbreviated symbol : F *

* Denotes h_{FE}

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CE0}	-50	V
Emitter-base voltage	V _{EB0}	-6	V
Collector current	I _c	-0.15	A (DC)
Collector power dissipation	HB50P15CT P _c	0.15	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-60	-	-	V	I _c = -50μA
Collector-emitter breakdown voltage	BV _{CE0}	-50	-	-	V	I _c = -1mA
Emitter-base breakdown voltage	BV _{EB0}	-6	-	-	V	I _E = -50μA
Collector cutoff current	I _{cBO}	-	-	-0.1	μA	V _{CB} = -60V
Emitter cutoff current	I _{EBO}	-	-	-0.1	μA	V _{EB} = -6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	-0.5	V	I _c /I _B = -50mA/-5mA
DC current transfer ratio	h _{FE}	120	-	390	-	V _{CE} = -6V, I _c = -1mA
Transition frequency	f _T	-	140	-	MHz	V _{CE} = -12V, I _E =2mA, f=100MHz
Output capacitance	C _{ob}	-	4.0	5.0	pF	V _{CB} = -12V, I _E =0A, f=1MHz

●Packaging specifications and h_{FE}

Type	h _{FE}	Package	Taping			
		Code	T146	T106	TL	T2L
		Basic ordering unit (pieces)	3000	3000	3000	8000
HB50P15CT		-	-	-	○	

●Electrical characteristic curves

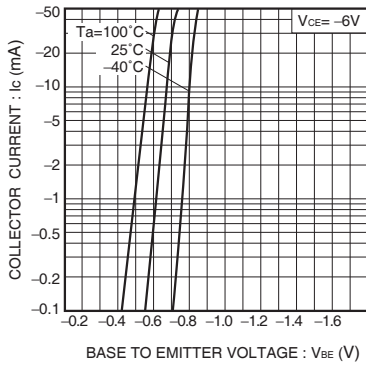


Fig.1 Grounded emitter propagation characteristics

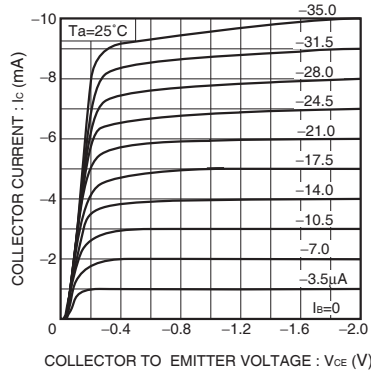


Fig.2 Grounded emitter output characteristics (I)

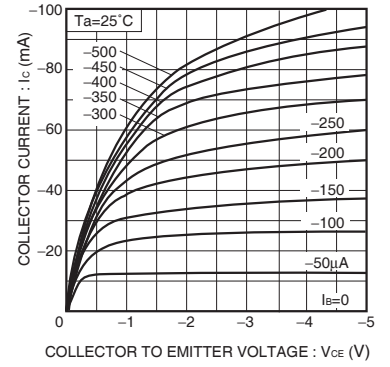


Fig.3 Grounded emitter output characteristics (II)

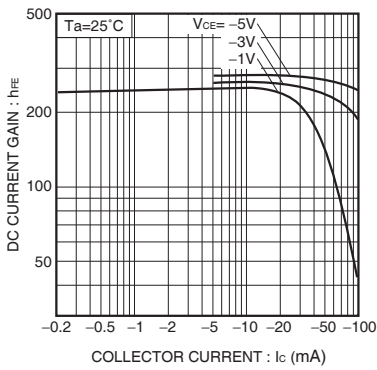


Fig.4 DC current gain vs. collector current (I)

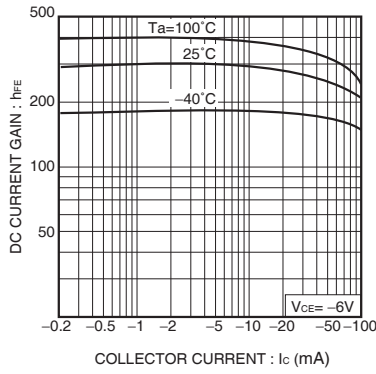


Fig.5 DC current gain vs. collector current (II)

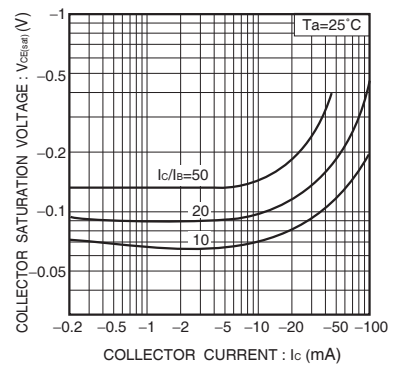


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

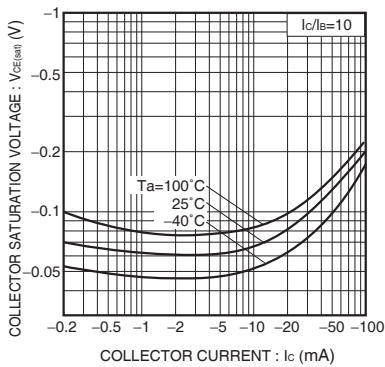


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

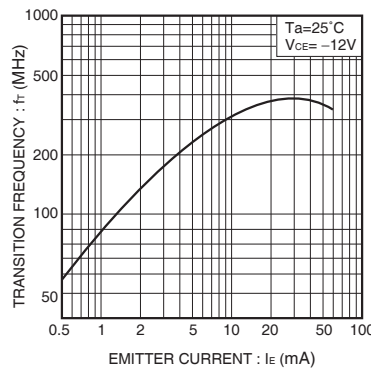


Fig.8 Gain bandwidth product vs. emitter current

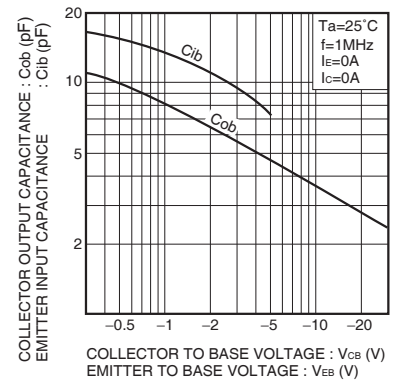


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage